



Support & training



HD3SS3411-Q1 SLASE82B – JUNE 2015 – REVISED MARCH 2024

HD3SS3411-Q1 One Channel Differential 2:1 Mux/Demux

1 Features

- Q100 automotive qualified
- Compatible with multiple interface standards including FPD link, LVDS, PCIE Gen II, III, XAUI, and USB3.1
- Operates up to 10Gbps
- Wide –3dB differential BW of approximately 7.5GHz
- Excellent dynamic characteristics (at 4GHz)
 - Insertion loss = -1.1dB
 - Return loss = –11.3dB
 - Off isolation = –19dB
- Bidirectional Mux/De-Mux differential switch
- Supports common-mode voltage 0V to 2V
- Single supply voltage V_{CC} of 3.3V ±10%
- Industrial temperature range of –40°C to 105°C

2 Applications

- Automotive infotainment
- · Industrial data switching
- Desktop and notebook PCs
- Server or storage area networks
- PCI express backplanes
- Shared I/O ports

3 Description

The HD3SS3411-Q1 is a high-speed bi-directional passive switch in multiplexer or demultiplexer configurations. Based on control pin SEL, the device provides switching of differential channels between Port B to Port A or Port C to Port A.

The HD3SS3411-Q1 is a generic analog differential passive switch that can work for any high speed interface application as long as it is biased at a common-mode voltage range of 0V to 2V and has differential signaling with differential amplitude up to 1800mVpp. The device offers adaptive tracking that allows users to keep the channel unchanged for the entire common-mode voltage range.

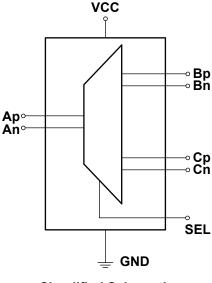
Excellent dynamic characteristics of the device allow high speed switching with minimum attenuation to the signal eye diagram with little added jitter. The HD3SS3411-Q1 consumes < 2mW of power when operational and has a shutdown mode exercisable by OEn pin resulting < 2μ W.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
HD3SS3411-Q1	RWA (WQFN, 14)	3.5mm × 3.5mm

(1) For more information, see Section 10.

(2) The package size (length × width) is a nominal value and includes pins, where applicable.



Simplified Schematic



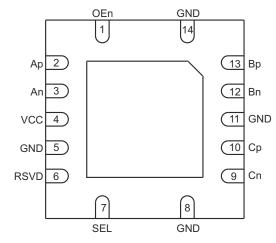
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4 Pin Configuration and Functions



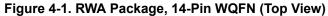


Table 4-1	Pin F	Functions
		uncuons

NAME	NO	TYPE ⁽¹⁾	DESCRIPTION	
Ар	2	I/O	Port A, High Speed Positive Signal	
An	3	I/O	Port A, High Speed Negative Signal	
Вр	13	I/O	Port B, High Speed Positive Signal	
Bn	12	I/O	Port B, High Speed Negative Signal	
Ср	10	I/O	Port C, High Speed Positive Signal	
Cn	9	I/O	Port C, High Speed Negative Signal	
GND	5,8,11,14, Pad	G	Ground	
OEn	1	I	Active Low Chip Enable L: Normal operation H: Shutdown	
RSVD	6	I/O	Reserved Pin – connect or pulldown to GND	
SEL	7	I	Port select pin L: Port A to Port B H: Port A to Port C	
VCC	4	Р	3.3V power	

 The high speed data ports incorporate 20kΩ pulldown resistors that are switched in when a port is not selected and switched out when the port is selected..

5 Specifications 5.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Supply voltage range (V _{CC})	Absolute minimum/maximum supply voltage range	-0.5	4	V
Voltage range	Differential I/O	-0.5	2.5	V
	Control pin	-0.5	V _{DD} + 0.5	v

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	±2000	V
V _(ESD)		Charged-device model (CDM), per AEC Q100-011	±500	v

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
V _{CC}	Supply voltage	3	3.6	V
VIH	Input high voltage (SEL, OEn Pin)	2	V _{CC}	V
VIL	Input low voltage (SEL OEn Pin)	-0.1	0.8	V
V _{Diff}	High speed signal pins differential voltage	0	1.8	V _{PP}
V _{CM}	Common mode voltage (differential pins)	0	2	V
T _A	Operating free-air temperature	-40	105	°C

5.4 Thermal Information

			LINUT
		14 PINS	UNIT
R _{θJA}	Junction-to-ambient thermal resistance	50.5	
R _{0JC(top)}	Junction-to-case (top) thermal resistance	63.1	
R _{θJB}	Junction-to-board thermal resistance	26.4	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	2.2	C/W
Ψ _{JB}	Junction-to-board characterization parameter	26.5	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	7.3	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



5.5 Electrical Characteristics

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
I _{CC}	Device active Current	V _{CC} = 3.3V, OEn = 0	I	0.6	0.8	mA	
I _{STDN}	Device shutdown Current	V _{CC} = 3.3V, OEn = 0		0.3	0.6	μA	
C _{ON}	Outputs ON Capacitance			0.6		pF	
R _{ON}	Output ON resistance	$V_{CC} = 3.3V; V_{CM} = 0V \text{ to } 2V;$ $I_{O} = -8mA$		5	8	Ω	
ΔR _{ON}	On resistance match between pairs of the same channel	$V_{CC} = 3.3V$; -0.35V $\leq V_{IN} \leq 2.35V$; $I_{O} = -8mA$			0.5	Ω	
R _(FLAT_ON)	On resistance flatness (R _{ON(MAX)} – R _{ON(MAIN)}	$V_{DD} = 3.3V; -0.35V \le V_{IN} \le 2.35V$			1	Ω	
I _{IH(CTRL)}	Input high current, control pins (SEL, OEn)				1	μA	
I _{IL(CTRL)}	Input low current, control pins (SEL, OEn)				1	μA	
		$\label{eq:alpha} \begin{array}{l} \mbox{[A/B/C][p/n] V_{IN} = 2V$ for selected port, A} \\ \mbox{and B with SEL= 0, and A and C with} \\ \mbox{SEL = V_{CC}} \end{array}$			1	μΑ	
I _{IH(HS)}	Input high current, high speed pins	$\begin{tabular}{lllllllllllllllllllllllllllllllllll$		100	140	μΑ	
I _{IL(HS)}	Input low current, high speed pins	[A/B/C][p/n]			1	μA	
High Speed	d Performance						
		f = 0.3MHz		-0.5			
IL	Differential Insertion Loss	f = 2.5GHz		-0.7		dB	
		f = 4GHz		-1.1			
BW	–3dB Bandwidth			7.5		GHz	
		f = 0.3MHz		-26.4	.4		
R _L	Differential return loss	f = 2.5GHz		-16.6		dB	
		f = 4GHz		-11.3			
		f = 0.3MHz		-75			
Ol	Differential OFF isolation	f = 2.5GHz		-22		dB	
		f = 4GHz		-19			
Xtalk	Differential Crosstalk	f = 4GHz		-35		dB	

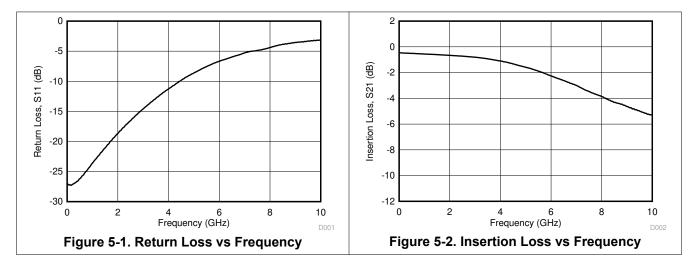
over operating free-air temperature range (unless otherwise noted)

5.6 Timing Requirements

		MIN	NOM	MAX	UNIT
t _{PD}	Switch propagation delay			80	ps
t _{SW}	Switching time			1	μs
t _{SK_INTRA}	Intra-pair output skew			5	ps



5.7 Typical Characteristics





6 Detailed Description

6.1 Overview

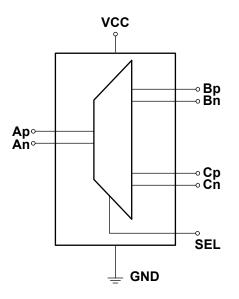
The HD3SS3411-Q1 is a high-speed bi-directional passive switch in mux or demux configurations. Based on control pin SEL, the device switches one differential channels between Port B or Port C to Port A.

The HD3SS3411-Q1 is a generic analog differential passive switch that can work for any high speed interface applications as long as it is biased at a common-mode voltage range of 0V to 2V and has differential signaling with differential amplitude up to 1800 mVpp. The device offers adaptive tracking that allows users to keep the channel unchanged for the entire common-mode voltage range.

PORT A CHANNEL	PORT B OR PORT C CHANNEL CONNECTED TO PORT A CHANNEL			
	SEL = L	SEL = H		
Ар	Вр	Ср		
An	Bn	Cn		

(1) The HD3SS3411-Q1 can tolerate polarity inversions for all differential signals on Ports A, B and C. Take care to ensure the same polarity is maintained on Port A vs. Port B/C.

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 Output Enable and Power Savings

The HD3SS3411-Q1 has two power modes, normal operating mode and shutdown mode. During shutdown mode, the device consumes very-little current to save the maximum power. The OEn control pin is used to toggle between the two modes.

HD3SS3411-Q1 consumes < 2 mW of power when operational and has a shutdown mode exercisable by the OEn pin resulting < 20 μ W.



6.4 Device Functional Modes

The OEn control pin selects the functional mode of HD3SS3411-Q1. To enter standby/shutdown mode, the OEn control pin is pulled high through a resistor and must remain high. For active or normal operation, pull the OEn control pin low to GND or dynamically control the OEn control pin to switch between H or L.

Table 6-2. Device Fower modes								
OEn	Device State	Signal Pins						
L	Normal	Normal						
Н	Shutdown	Tri-stated						

Table 6-2. Device Power Modes



7 Application and Implementation

Note

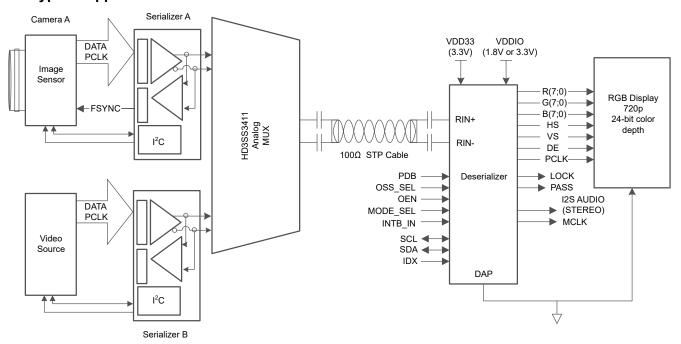
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

HD3SS3411-Q1 mux channels have independent adaptive common mode tracking allowing RX and TX paths to have different common-mode voltage simplifying system implementation and avoiding inter-operational issues.

HD3SS3411-Q1 mux does not provide common mode biasing for the channel. Therefore, it is required that the device is biased from either side for all active channels.

The HD3SS3411 supports several high-speed data protocols with a differential amplitude of < 1800 mVpp and a common-mode voltage of < 2V, as with USB 3.1 and DisplayPort 1.3. The one select input (SEL) pin can be controlled by an available GPIO pin within a system or from a microcontroller.



7.2 Typical Application

Figure 7-1. FPD Link III Application

7.2.1 Design Requirements

For this design example, use the values shown in Table 7-1.

PARAMETER	VALUE
V _{CC} voltage	3.3V
Ap/n, Bp/n, Cp/n CM input voltage	0V to 2V
SEL/OEn pin max voltage for low	0V
SEL/OEn pin min voltage for high	3.3V

7.2.2 Detailed Design Procedure

7.2.2.1 AC Coupling Capacitors

Many interfaces require AC coupling between the transmitter and receiver. The 0402 capacitors are the preferred option to provide AC coupling, and the 0603 size capacitors will also work. Avoid the 0805 size capacitors and C-packs when possible. Symmetric placement is best for AC coupling capacitors. TI recommends a capacitor value of 0.1μ F. Make sure the capacitor value matches the ± signal pair. Make sure the placement is along the TX pairs on the system board, which are usually routed on the top layer of the board.

There are several placement options for the AC coupling capacitors. Because the switch requires a bias voltage, the capacitors must only be placed on one side of the switch. If the capacitors are placed on both sides of the switch, make sure to provide a biasing voltage. In Figure 7-2, the coupling capacitors are placed between the switch and endpoint. In this situation, the switch is biased by the system/host controller.

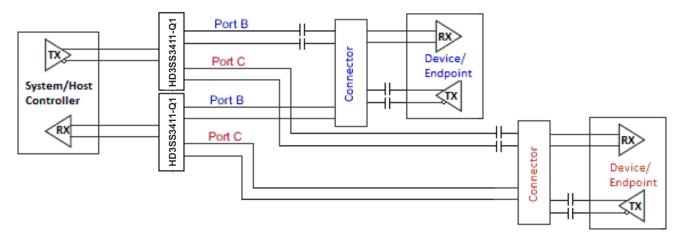


Figure 7-2. AC Coupling Capacitors Between Switch TX and Endpoint TX



In Figure 7-3, the coupling capacitors are placed on the host transmit pair and endpoint transmit pair. In this situation, the switch on the top is biased by the endpoint and the lower switch is biased by the host controller.

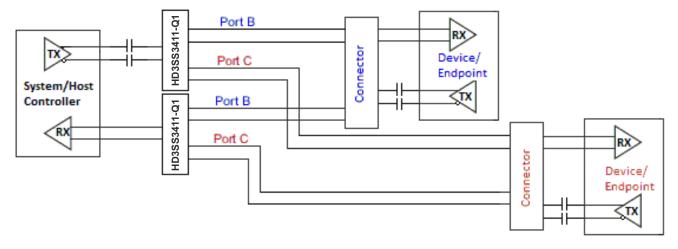


Figure 7-3. AC Coupling Capacitors on Host TX and Endpoint TX

If the common-mode voltage in the system is higher than 2V, the coupling capacitors are placed on both sides of the switch (shown in Figure 7-4). A biasing voltage of less than 2V is required in this case.

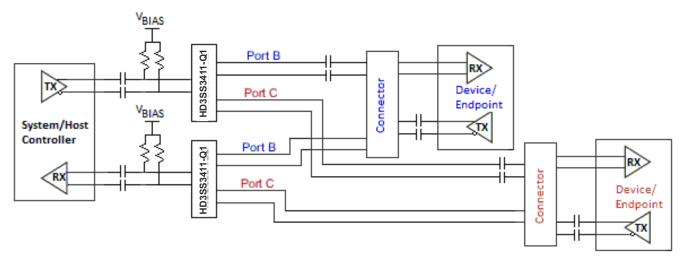
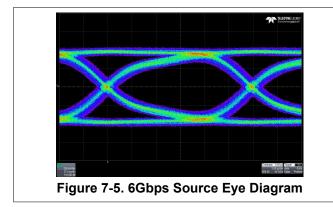
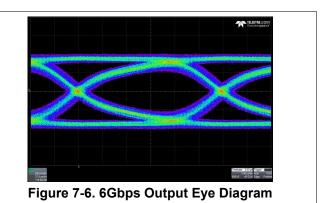


Figure 7-4. AC Coupling Capacitors on Both Sides of Switch



7.2.3 Application Curves





7.3 Power Supply Recommendations

There is no power supply sequence required for HD3SS3411-Q1. However, TI recommends that OEn is asserted low after device supply V_{CC} is stable and in specifications. TI also recommends that ample decoupling capacitors are placed at the device V_{CC} near the pin.

7.4 Layout

7.4.1 Layout Guidelines

7.4.1.1 Critical Routes

- The high speed differential signals must be routed with great care to minimize signal quality degradation between the connector and the source or sink of the high speed signals by following the guidelines provided in this document. Depending on the configuration schemes, the speed of each differential pair can reach a maximum speed of 10Gbps. These signals are to be routed first before other signals with highest priority.
- Make sure each differential pair is routed together with controlled differential impedance of 85Ω to 90Ω and 50Ω common-mode impedance. Keep away from other high speed signals. TI recommends to keep the number of vias to a minimum. Separate each pair from adjacent pairs by at least 3 times the signal trace width. Route all differential pairs on the same group of layers (outer layers or inner layers) if not on the same layer. No 90 degree turns on any of the differential pairs. If bends are used on high speed differential pairs, make sure the angle of the bend is greater than 135 degrees.
- · Length matching:
 - Keep high speed differential pairs lengths within 5 mil of each other to keep the intra-pair skew minimum.
 The inter-pair matching of the differential pairs is not as critical as intra-pair matching.
- Keep high speed differential pair traces adjacent to ground plane.
- Do not route differential pairs over any plane split.
- Place the ESD components on the high speed differential lanes as close to the connector as possible in a pass through manner without stubs on the differential path.
- For ease of routing, the P and N connection of the USB3.1 differential pairs to the HD3SS3411-Q1 pins can be swapped.

7.4.1.2 General Routing/Placement Rules

- Follow 20H rule (H is the distance to ref-plane) for separation of the high speed trace from the edge of the plane.
- Minimize parallelism of high speed clocks and other periodic signal traces to high speed lines.
- Route all differential pairs on the top or bottom layer (microstrip traces) if possible or on the same group of layers. Only use vias in the breakout region of the device if vias are necessary for routing. Avoid using vias in the main region of the board at all cost. Use a ground reference via next to signal via. Distance between ground reference via and signal need to be calculated to have similar impedance as traces.
- Make sure not all differential signals are routed over a plane split. Changing signal layers is preferable to crossing plane splits.





- Use of and proper placement of stitching caps when split plane crossing is unavoidable to account for high frequency return current path.
- Route differential traces over a continuous plane with no interruptions.
- Do not route differential traces under power connectors or other interface connectors, crystals, oscillators, or any magnetic source.
- Route traces away from etching areas like pads, vias, and other signal traces. Try to maintain a 20 mil keep out distance where possible.
- Place the decoupling caps next to each power terminal on the HD3SS3411-Q1. Take care to minimize the stub length of the trace connecting the capacitor to the power pin.
- Avoid sharing vias between multiple decoupling caps.
- Place vias as close as possible to the decoupling cap solder pad.
- Widen VCC/GND planes to reduce effect of static and dynamic IR drop.

7.4.2 Layout Example

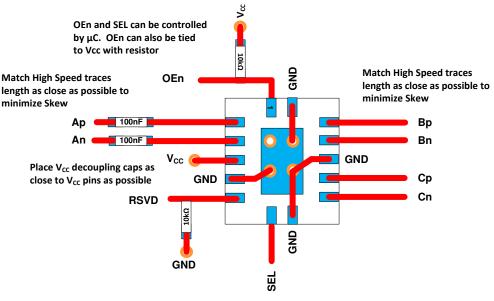


Figure 7-7. Layout



8 Device and Documentation Support

8.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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8.3 Trademarks

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8.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	Changes from Revision A (June 2015) to Revision B (March 2024)						
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1					
•	Changed the maximum t _{SW} switching time from 0.5ns to 1µs	<mark>5</mark>					

С	Changes from Revision * (June 2015) to Revision A (July 2015)					
•	Changed the "Operating free-air Temperature" MAX value from: 85°C to: 105°C in Recommended Ope	rating				
	Conditions	4				
•	Changed the MAX value of $R_{(FLAT_ON)}$ from: 0.5 Ω to: 1 Ω in the <i>Electrical Characteristics</i>					

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
HD3SS3411TRWARQ1	ACTIVE	WQFN	RWA	14	3000	RoHS & Green	(6) NIPDAU	Level-2-260C-1 YEAR	-40 to 105	3411Q	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF HD3SS3411-Q1 :



www.ti.com

11-Dec-2023

Catalog : HD3SS3411

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product



www.ti.com

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Dovico	Packago	Packag
*All dimensions are nominal		

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	` '	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
HD3SS3411TRWARQ1	WQFN	RWA	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q2



www.ti.com

PACKAGE MATERIALS INFORMATION

11-Dec-2023



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
HD3SS3411TRWARQ1	WQFN	RWA	14	3000	346.0	346.0	33.0

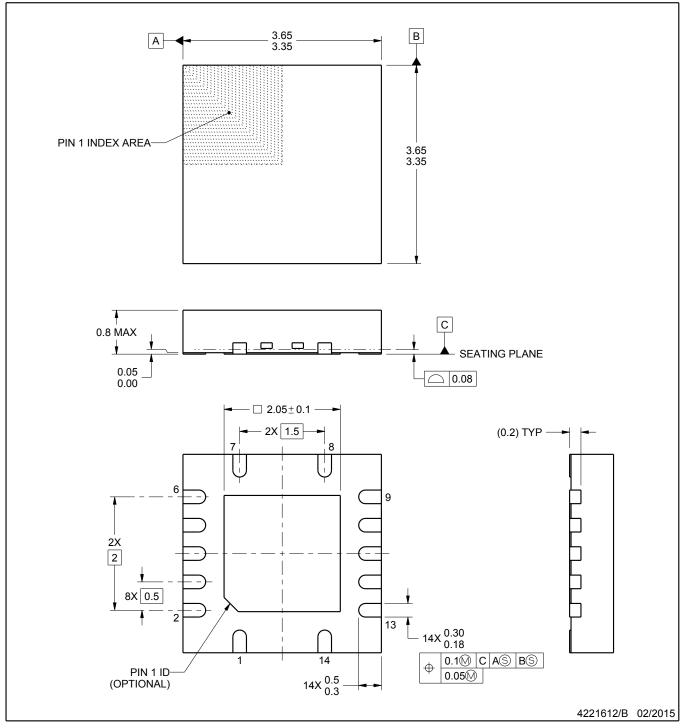
RWA0014A



PACKAGE OUTLINE

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
 The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

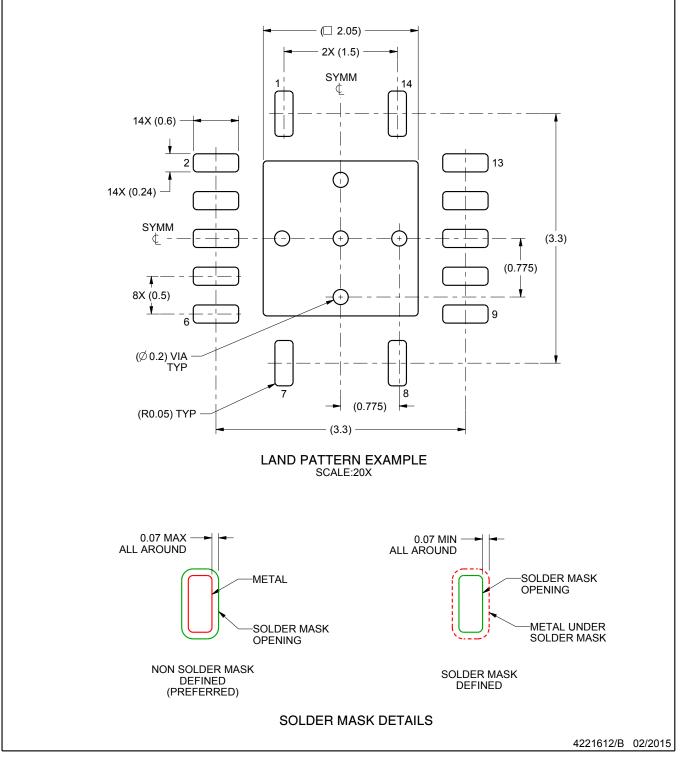


RWA0014A

EXAMPLE BOARD LAYOUT

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

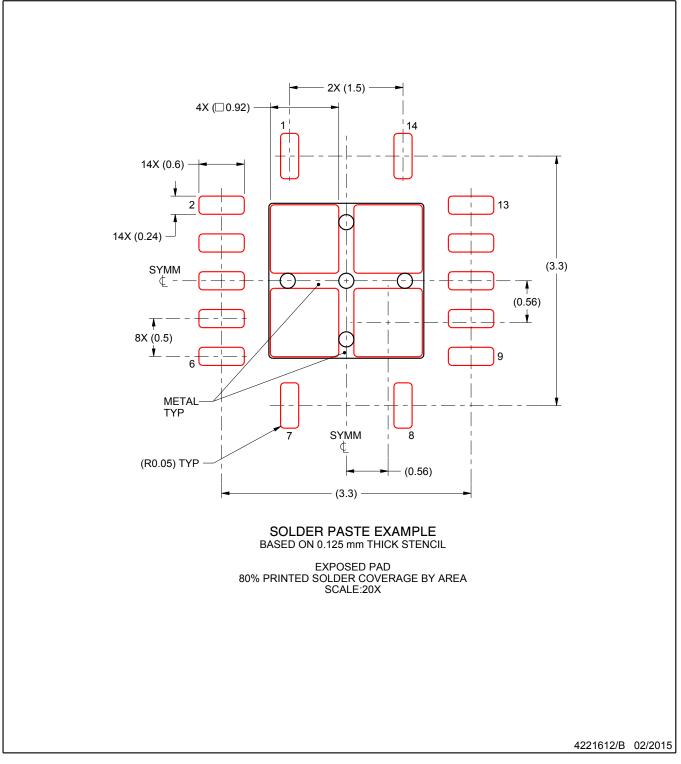


RWA0014A

EXAMPLE STENCIL DESIGN

WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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